



(51) International Patent Classification:

C30B 15/10 (2006.01) *C30B 35/00* (2006.01)
C30B 29/06 (2006.01) *C30B 15/22* (2006.01)

(21) International Application Number:

PCT/EP2012/063494

(22) International Filing Date:

10 July 2012 (10.07.2012)

(25) Filing Language:

English

(26) Publication Language:

English

(30) Priority Data:

2011-283330 26 December 2011 (26.12.2011) JP

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(81) Designated States (unless otherwise indicated, for every kind of national protection available): AE, AG, AL, AM, AO, AT, AU, AZ, BA, BB, BG, BH, BR, BW, BY, BZ, CA, CH, CL, CN, CO, CR, CU, CZ, DE, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IS, JP, KE, KG, KM, KN, KP, KR, KZ, LA, LC, LK, LR, LS, LT, LU, LY, MA, MD, ME, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PE, PG, PH, PL, PT, QA, RO, RS, RU, RW, SC, SD, SE, SG, SK, SL, SM, ST, SV, SY, TH, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, ZA, ZM, ZW.

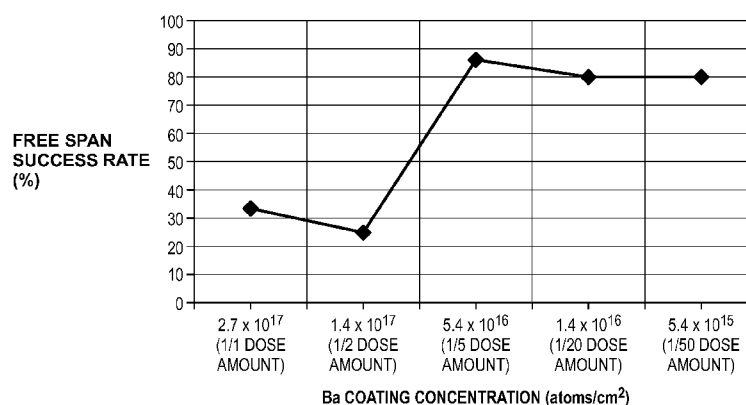
(84) Designated States (unless otherwise indicated, for every kind of regional protection available): ARIPO (BW, GH, GM, KE, LR, LS, MW, MZ, NA, RW, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, RU, TJ, TM), European (AL, AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, LV, MC, MK, MT, NL, NO, PL, PT, RO, RS, SE, SI, SK, SM, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Published:

— with international search report (Art. 21(3))

(54) Title: METHOD FOR MANUFACTURING SINGLE-CRYSTAL SILICON

Fig. 5



(57) Abstract: There is provided a method for manufacturing single-crystal silicon that makes it possible to reduce occurrence of dislocation of the single-crystal silicon when the single-crystal silicon is grown using a multi-pulling method for pulling up a plurality of pieces of single-crystal silicon from a material melt in an identical crucible. Solving Means A method for manufacturing single-crystal silicon is directed to a method for manufacturing a single-crystal silicon (1) using the multi-pulling method for pulling up a plurality of pieces of single-crystal silicon (1) from a material melt (7) in an identical crucible (8) within a chamber by a Czochralski method, the method including the step of omitting at least a part of formation of a tail part of the single-crystal silicon (1) and separating the single-crystal silicon from the material melt, wherein an amount of addition of barium formed on an inner wall of crucible (8) is controlled within a certain range.